

# Complementary MOSFET

## ELM16604EA-S

### ■ General Description

ELM16604EA-S uses advanced trench technology to provide excellent  $R_{ds(on)}$  and low gate charge.

### ■ Features

- |  |   |
|--|---|
| N-channel                                | P-channel                               |
| • $V_{ds}=20V$                           | $V_{ds}=-20V$                           |
| • $I_d=3.4A(V_{gs}=4.5V)$                | $I_d=-2.5A(V_{gs}=-4.5V)$               |
| • $R_{ds(on)} < 60m\Omega(V_{gs}=4.5V)$  | $R_{ds(on)} < 110m\Omega(V_{gs}=-4.5V)$ |
| • $R_{ds(on)} < 75m\Omega(V_{gs}=2.5V)$  | $R_{ds(on)} < 140m\Omega(V_{gs}=-2.5V)$ |
| • $R_{ds(on)} < 100m\Omega(V_{gs}=1.8V)$ | $R_{ds(on)} < 200m\Omega(V_{gs}=-1.8V)$ |

### ■ Maximum Absolute Ratings

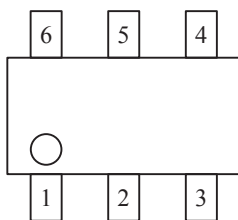
| Parameter                              | Symbol         | N-ch (Max.)      | P-ch (Max.) | Unit       | Note |
|--|----------------|------------------|-------------|------------|------|
| Drain-source voltage                   | $V_{ds}$       | 20               | -20         | V          |      |
| Gate-source voltage                    | $V_{gs}$       | $\pm 8$          | $\pm 8$     | V          |      |
| Continuous drain current               | $I_d$          | $T_a=25^\circ C$ | -2.5        | A          | 1    |
|  |                | $T_a=70^\circ C$ | -2.0        |            |      |
| Pulsed drain current                   | $I_{dm}$       | 15               | -15         | A          | 2    |
| Power dissipation                      | $P_d$          | $T_a=25^\circ C$ | 1.15        | W          |      |
|  |                | $T_a=70^\circ C$ | 0.73        |            |      |
| Junction and storage temperature range | $T_j, T_{stg}$ | -55 to 150       | -55 to 150  | $^\circ C$ |      |

### ■ Thermal Characteristics

| Parameter                   | Symbol          | Device | Typ.            | Max. | Unit | Note         |
|-----------------------------|-----------------|--------|-----------------|------|------|--------------|
| Maximum junction-to-ambient | $R_{\theta ja}$ | N-ch   | $t \leq 10s$    | 78   | 110  | $^\circ C/W$ |
| Maximum junction-to-ambient |                 |        | Steady-state    | 106  | 150  | $^\circ C/W$ |
| Maximum junction-to-lead    | Steady-state    |        | $R_{\theta jl}$ | 64   | 80   | $^\circ C/W$ |
| Maximum junction-to-ambient | $R_{\theta ja}$ | P-ch   | $t \leq 10s$    | 78   | 110  | $^\circ C/W$ |
| Maximum junction-to-ambient |                 |        | Steady-state    | 106  | 150  | $^\circ C/W$ |
| Maximum junction-to-lead    | Steady-state    |        | $R_{\theta jl}$ | 64   | 80   | $^\circ C/W$ |

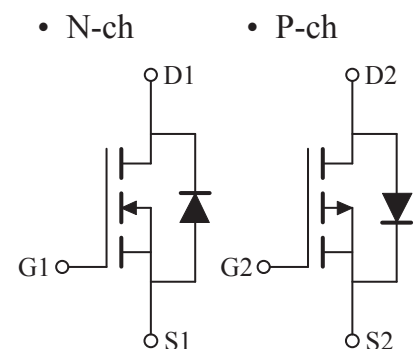
### ■ Pin configuration

SOT-26(TOP VIEW)



| Pin No. | Pin name |
|---------|----------|
| 1       | GATE1    |
| 2       | SOURCE2  |
| 3       | GATE2    |
| 4       | DRAIN2   |
| 5       | SOURCE1  |
| 6       | DRAIN1   |

### ■ Circuit



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### ■ Electrical Characteristics (N-ch)

Ta=25°C

| Parameter                          | Symbol  | Conditions                 | Min.     | Typ. | Max. | Unit |
|------------------------------------|---------|----------------------------|----------|------|------|------|
| <b>STATIC PARAMETERS</b>           |         |                            |          |      |      |      |
| Drain-source breakdown voltage     | BVdss   | Id=250μA, Vgs=0V           | 20       |      |      | V    |
| Zero gate voltage drain current    | Idss    | Vds=16V, Vgs=0V            |          |      | 1    | μA   |
|                                    |         |                            | Tj=55°C  |      | 5    |      |
| Gate-body leakage current          | Igss    | Vds=0V, Vgs=±8V            |          |      | 100  | nA   |
| Gate threshold voltage             | Vgs(th) | Vds=Vgs, Id=250μA          | 0.4      | 0.6  | 1.0  | V    |
| On state drain current             | Id(on)  | Vgs=4.5V, Vds=5V           | 15       |      |      | A    |
| Static drain-source on-resistance  | Rds(on) | Vgs=4.5V, Id=3.4A          |          | 46   | 60   | mΩ   |
|                                    |         |                            | Tj=125°C |      | 63   |      |
|                                    |         | Vgs=2.5V, Id=3A            |          | 57   | 75   |      |
|                                    |         | Vgs=1.8V, Id=2A            |          | 72   | 100  |      |
| Forward transconductance           | Gfs     | Vds=5V, Id=3.4A            |          | 10   |      | S    |
| Diode forward voltage              | Vsd     | Is=1A, Vgs=0V              |          | 0.76 | 1.00 | V    |
| Max.body-diode continuous current  | Is      |                            |          |      | 2    | A    |
| <b>DYNAMIC PARAMETERS</b>          |         |                            |          |      |      |      |
| Input capacitance                  | Ciss    |                            |          | 436  | 570  | pF   |
| Output capacitance                 | Coss    | Vgs=0V, Vds=10V, f=1MHz    |          | 66   |      | pF   |
| Reverse transfer capacitance       | Crss    |                            |          | 44   |      | pF   |
| Gate resistance                    | Rg      | Vgs=0V, Vds=0V, f=1MHz     |          | 3    | 4    | Ω    |
| <b>SWITCHING PARAMETERS</b>        |         |                            |          |      |      |      |
| Total gate charge                  | Qg      |                            |          | 6.2  | 8.1  | nC   |
| Gate-source charge                 | Qgs     | Vgs=4.5V, Vds=10V, Id=3.4A |          | 1.6  |      | nC   |
| Gate-drain charge                  | Qgd     |                            |          | 0.5  |      | nC   |
| Turn-on delay time                 | td(on)  |                            |          | 5.5  |      | ns   |
| Turn-on rise time                  | tr      | Vgs=5V, Vds=10V            |          | 6.3  |      | ns   |
| Turn-off delay time                | td(off) | RI=3Ω, Rgen=3Ω             |          | 40.0 |      | ns   |
| Turn-off fall time                 | tf      |                            |          | 12.7 |      | ns   |
| Body-diode reverse recovery time   | trr     | If=3.4A, dl/dt=100A/μs     |          | 12.3 | 16.0 | ns   |
| Body-diode reverse recovery charge | Qrr     | If=3.4A, dl/dt=100A/μs     |          | 3.5  |      | nC   |

#### NOTE :

1. The value of Rθja is measured with the device mounted on 1in<sup>2</sup> FR-4 board of 2oz. Copper, in still air environment with Ta=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The Rθja is the sum of the thermal impedance from junction to lead Rθjl and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with Ta=25°C. The SOA curve provides a single pulse rating.

# Complementary MOSFET

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## ■ Typical Electrical and Thermal Characteristics (N-ch)

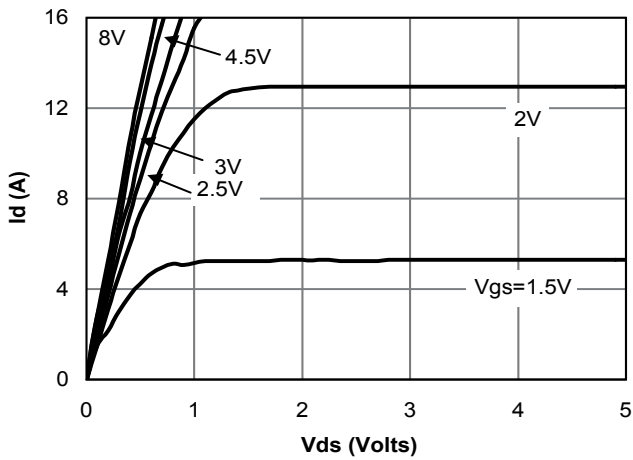


Fig 1: On-Region Characteristics

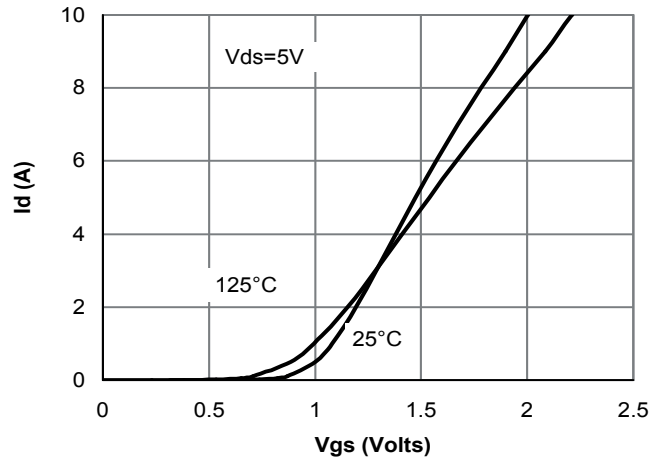


Figure 2: Transfer Characteristics

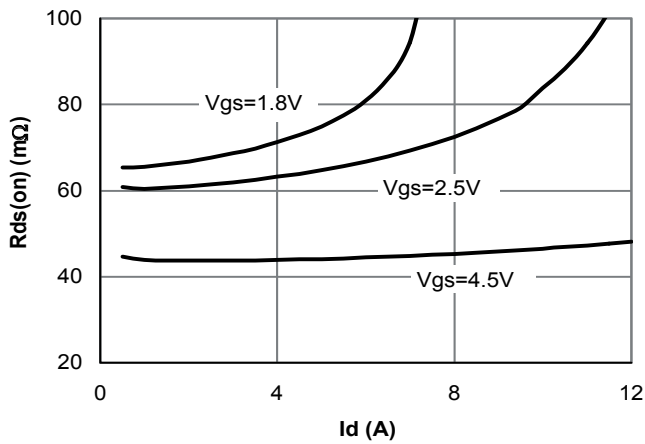


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

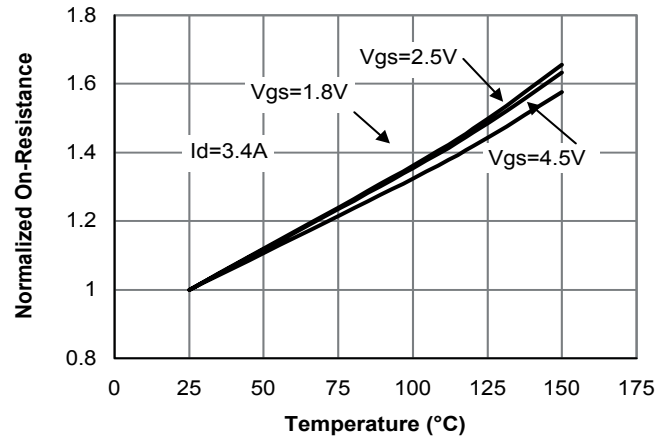


Figure 4: On-Resistance vs. Junction Temperature

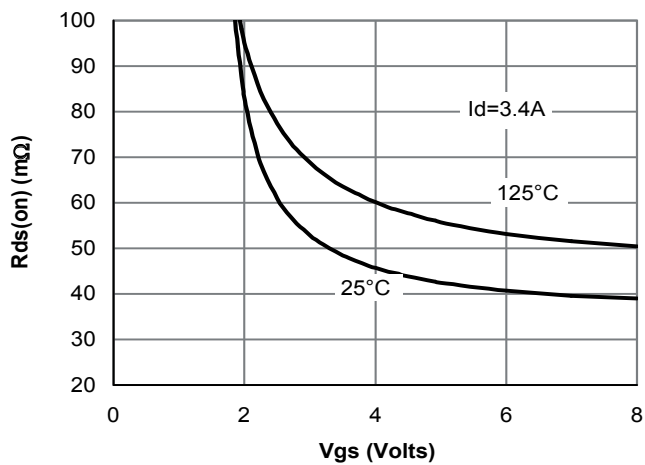


Figure 5: On-Resistance vs. Gate-Source Voltage

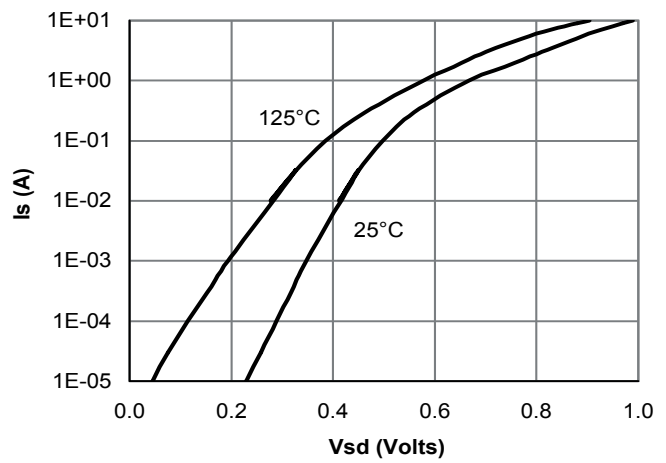


Figure 6: Body-Diode Characteristics

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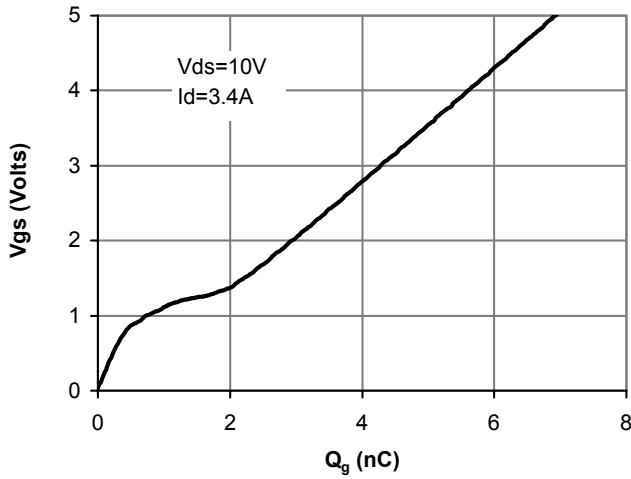


Figure 7: Gate-Charge Characteristics

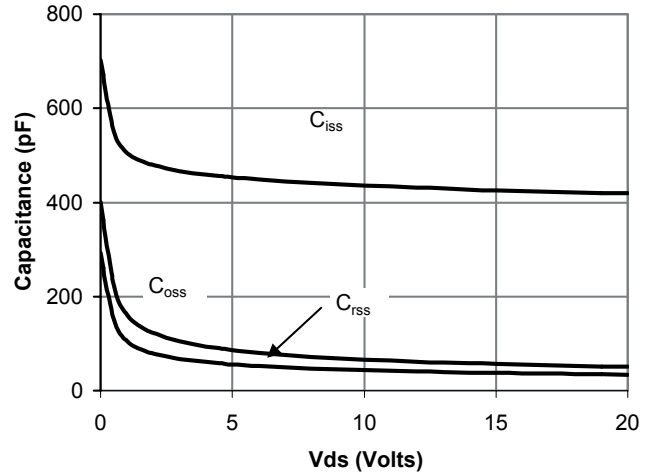


Figure 8: Capacitance Characteristics

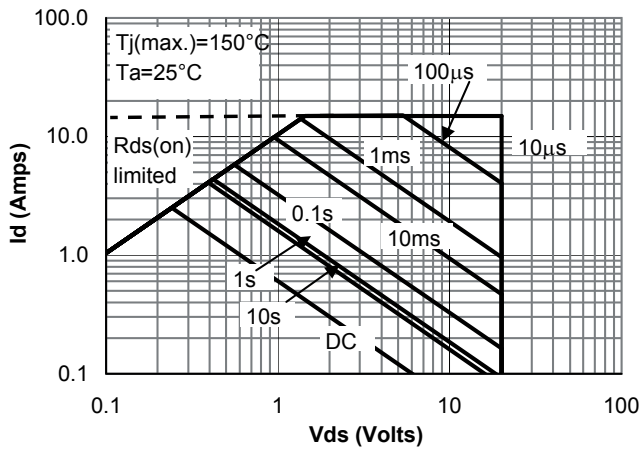


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

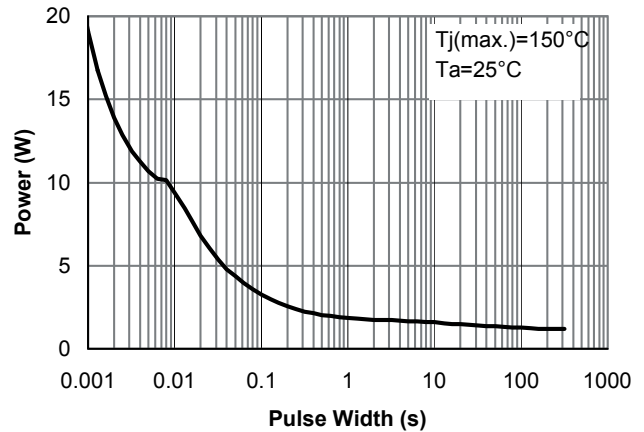


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

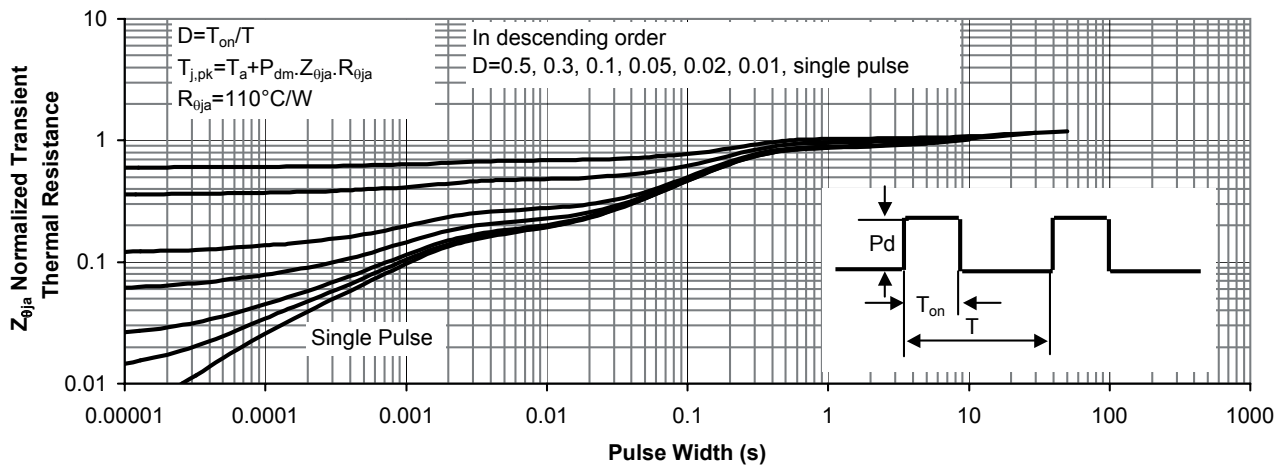


Figure 11: Normalized Maximum Transient Thermal Impedance

# Complementary MOSFET

## ELM16604EA-S

### ■ Electrical Characteristics (P-ch)

Ta=25°C

| Parameter                          | Symbol  | Conditions                              | Min.     | Typ.  | Max.  | Unit |
|------------------------------------|---------|---|----------|-------|-------|------|
| <b>STATIC PARAMETERS</b>           |         |   |          |       |       |      |
| Drain-source breakdown voltage     | BVdss   | Id=-250μA, Vgs=0V                       | -20      |       |       | V    |
| Zero gate voltage drain current    | Idss    | Vds=-16V, Vgs=0V                        |          |       | -1    | μA   |
|                                    |         | Tj=55°C                                 |          |       | -5    |      |
| Gate-body leakage current          | Igss    | Vds=0V, Vgs=±8V                         |          |       | ±100  | nA   |
| Gate threshold voltage             | Vgs(th) | Vds=Vgs, Id=-250μA                      | -0.30    | -0.55 | -1.00 | V    |
| On state drain current             | Id(on)  | Vgs=-4.5V, Vds=-5V                      | -15      |       |       | A    |
| Static drain-source on-resistance  | Rds(on) | Vgs=-4.5V                               |          | 86    | 110   | mΩ   |
|                                    |         | Id=-2.5A                                | Tj=125°C | 116   | 145   |      |
|                                    |         | Vgs=-2.5V, Id=-2A                       |          | 113   | 140   | mΩ   |
|                                    |         | Vgs=-1.8V, Id=-1A                       |          | 151   | 200   | mΩ   |
| Forward transconductance           | Gfs     | Vds=-5V, Id=-3A                         | 4        | 6     |       | S    |
| Diode forward voltage              | Vsd     | Is=-1A, Vgs=0V                          |          | -0.78 | -1.00 | V    |
| Max. body-diode continuous current | Is      |   |          |       | -2    | A    |
| <b>DYNAMIC PARAMETERS</b>          |         |   |          |       |       |      |
| Input capacitance                  | Ciss    |   |          | 540   | 700   | pF   |
| Output capacitance                 | Coss    | Vgs=0V, Vds=-10V, f=1MHz                |          | 72    |       | pF   |
| Reverse transfer capacitance       | Crss    |   |          | 49    |       | pF   |
| Gate resistance                    | Rg      | Vgs=0V, Vds=0V, f=1MHz                  |          | 12.0  | 15.6  | Ω    |
| <b>SWITCHING PARAMETERS</b>        |         |   |          |       |       |      |
| Total gate charge                  | Qg      | Vgs=-4.5V, Vds=-10V<br>Id=-2.5A         |          | 6.1   | 8.0   | nC   |
| Gate-source charge                 | Qgs     |   |          | 0.6   |       | nC   |
| Gate-drain charge                  | Qgd     |   |          | 1.6   |       | nC   |
| Turn-on delay time                 | td(on)  | Vgs=-4.5V, Vds=-10V<br>Rl=3.9Ω, Rgen=3Ω |          | 10    |       | ns   |
| Turn-on rise time                  | tr      |   |          | 12    |       | ns   |
| Turn-off delay time                | td(off) |   |          | 44    |       | ns   |
| Turn-off fall time                 | tf      |   |          | 22    |       | ns   |
| Body diode reverse recovery time   | trr     | If=-2.5A, dl/dt=100A/μs                 |          | 21.0  | 28.0  | ns   |
| Body diode reverse recovery charge | Qrr     | If=-2.5A, dl/dt=100A/μs                 |          | 7.5   |       | nC   |

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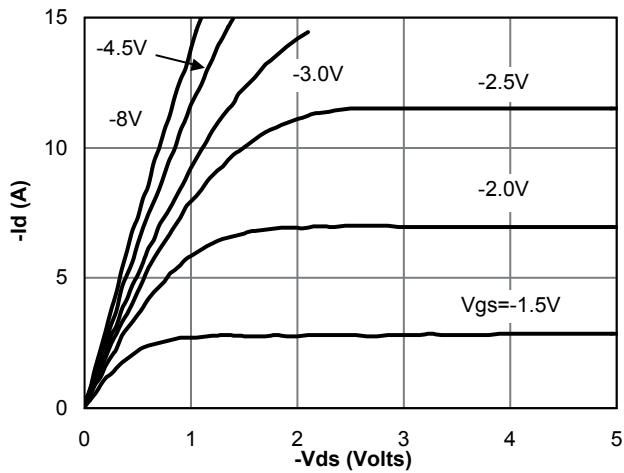


Fig 1: On-Region Characteristics

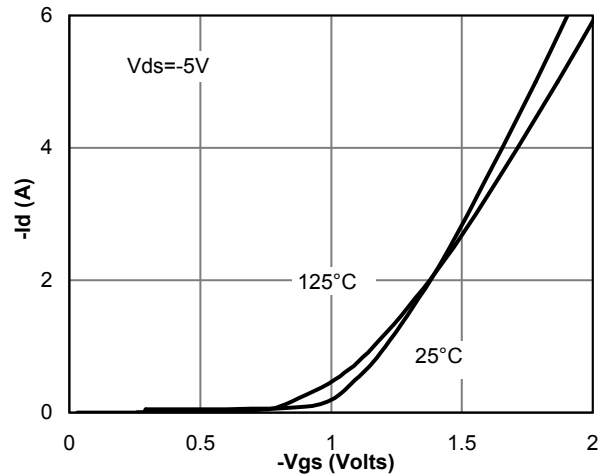


Figure 2: Transfer Characteristics

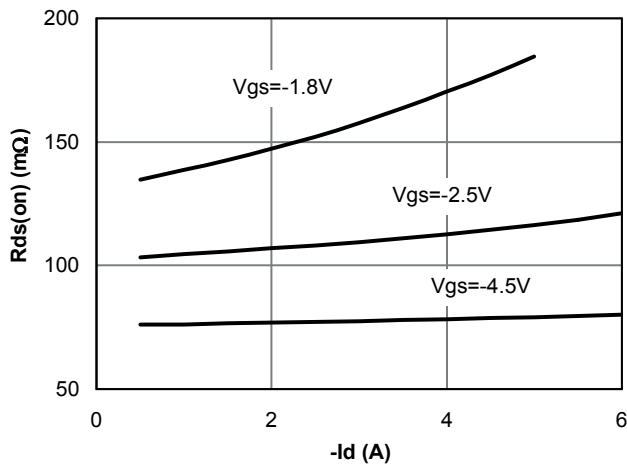


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

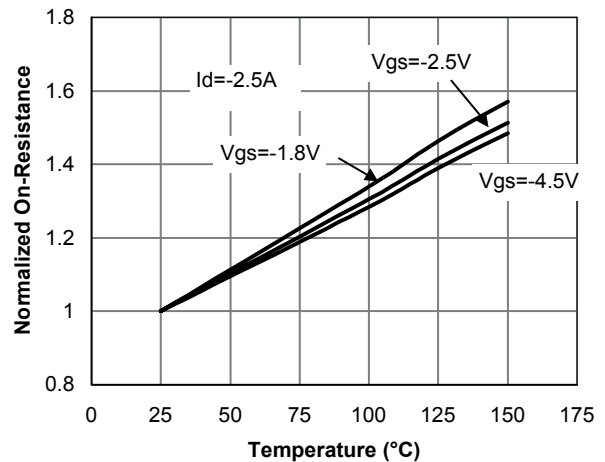


Figure 4: On-Resistance vs. Junction Temperature

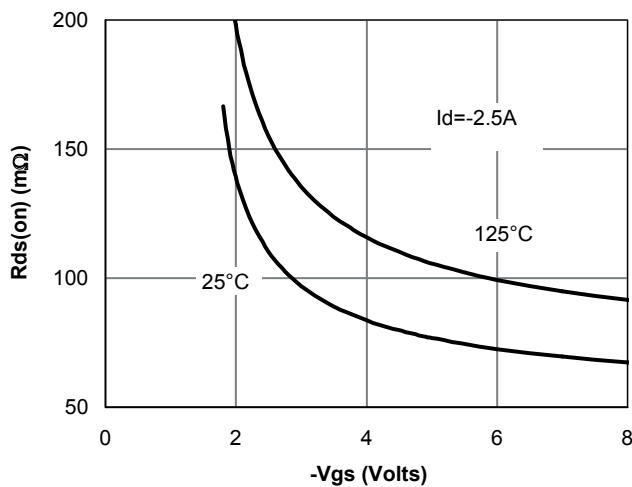


Figure 5: On-Resistance vs. Gate-Source Voltage

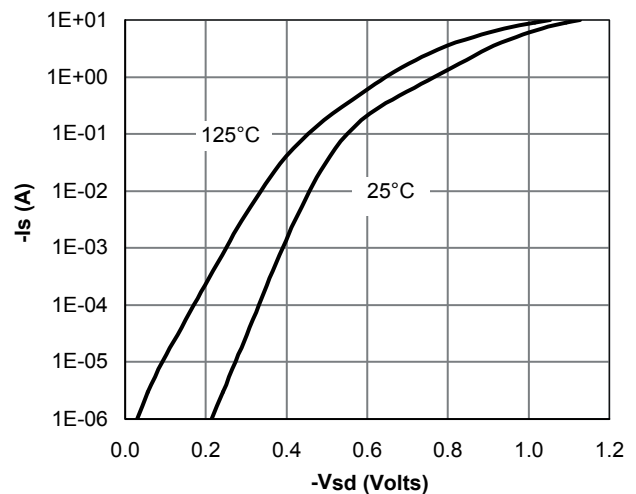


Figure 6: Body-Diode Characteristics

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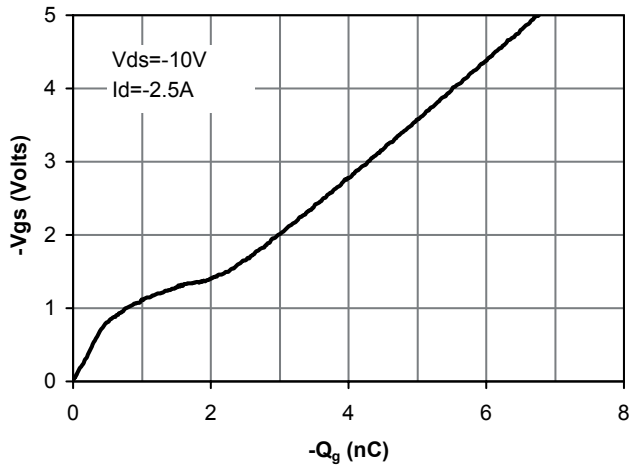


Figure 7: Gate-Charge Characteristics

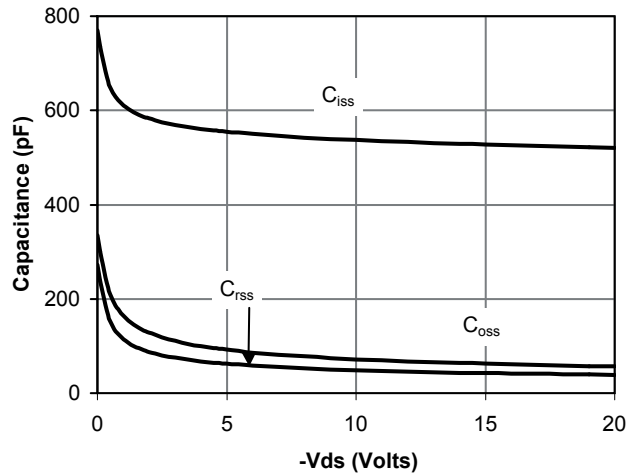


Figure 8: Capacitance Characteristics

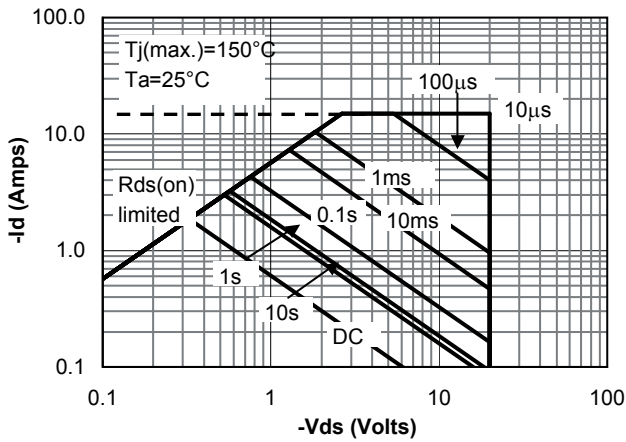


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

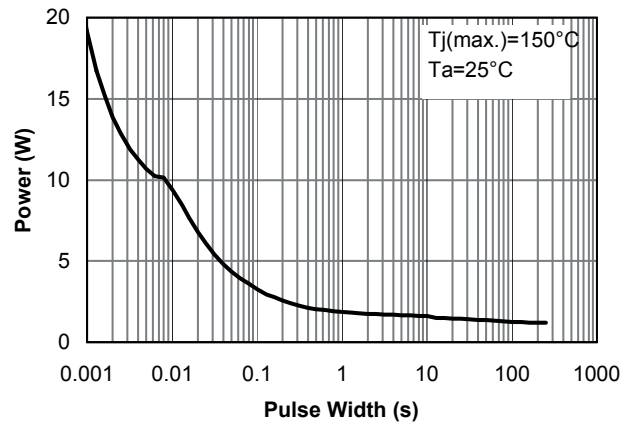


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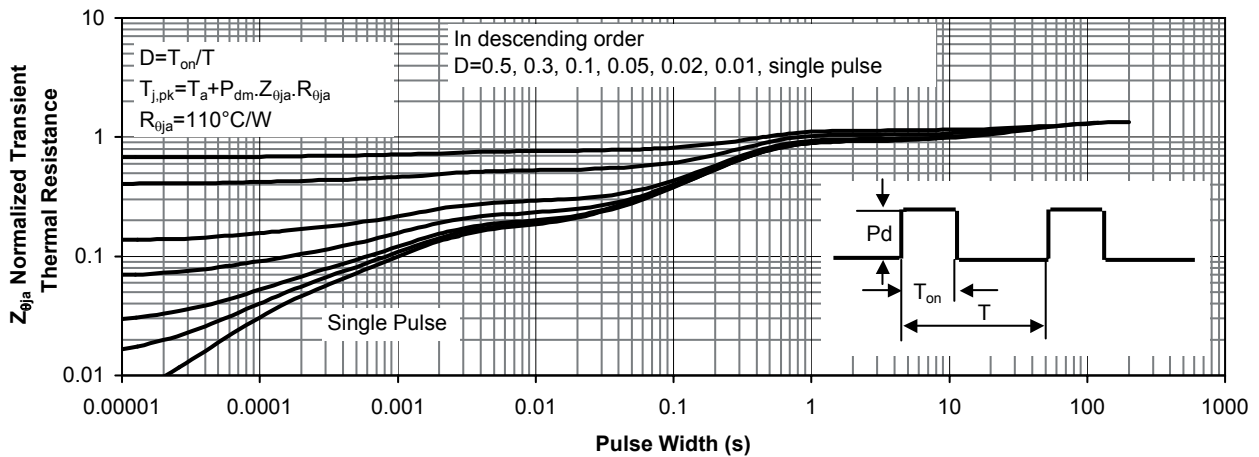


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